

<b>SANYO</b>	No.4112	<b>2SK1740</b>
		N-Channel Junction Silicon FET HF amplifiers low frequency amplifiers analog switches

**Features**

- Adoption of FBET process.
- Large  $|Y_{fs}|$ .
- Small Ciss.
- Small-sized package permitting 2SK1740-applied sets to be made small and slim.

**Absolute Maximum Ratings at Ta = 25°C**

			unit
Drain to Source Voltage	$V_{DSX}$	40	V
Gate to Drain Voltage	$V_{GDS}$	-40	V
Gate Current	$I_G$	10	mA
Drain Current	$I_D$	75	mA
Allowable Power Dissipation	$P_D$	250	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55 to +150	°C

**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
G-D Breakdown Voltage	$V_{(BR)GDS}$	$I_G = -10\mu A, V_{DS} = 0$	-40			V
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS} = -20V, V_{DS} = 0$			-1.0	nA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10V, I_D = 100\mu A$	-2.0	-3.0	-5.0	V
Drain Current	$I_{DSS}^*$	$V_{DS} = 10V, V_{GS} = 0$	40*		75*	mA
Forward Transfer Admittance	$ Y_{fs} $ (1)	$V_{DS} = 10V, I_D = 10mA, f = 1kHz$	10	15		mS
		$V_{DS} = 10V, V_{GS} = 0, f = 1kHz$	22	30		mS
Input Capacitance	$C_{iss}$	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$		11		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$		2.5		pF
Noise Figure	NF	$V_{DS} = 10V, R_g = 1k\Omega, I_D = 1mA, f = 1kHz$		1.5		dB
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = 10mA, V_{GS} = 0$		30		$\Omega$

\* : Pulse Test Pulse Width  $\leq 2ms$

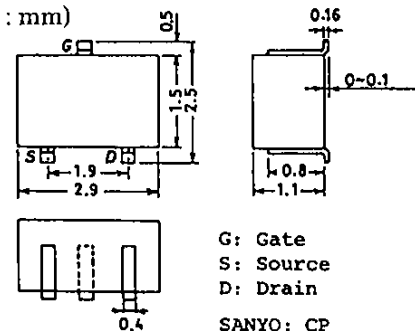
※ : The 2SK1740 is classified by  $I_{DSS}$  as follows (unit : mA)

40	3	52	48	4	63	57	5	75
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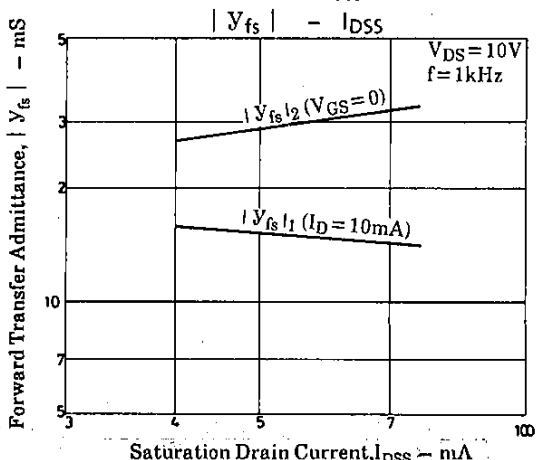
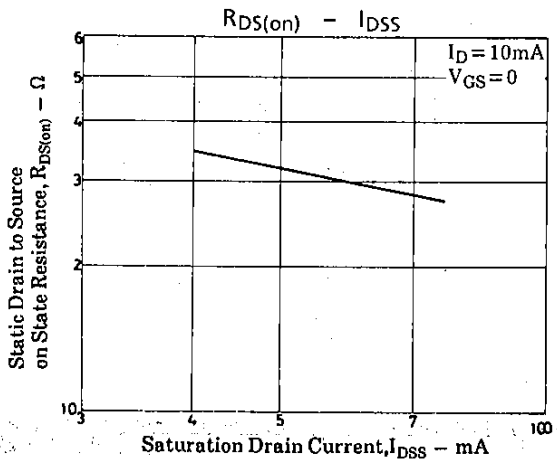
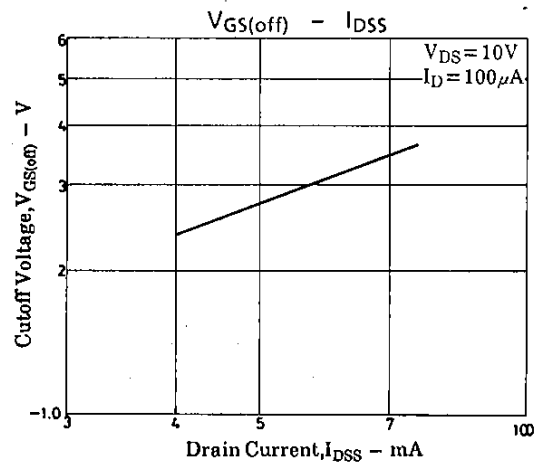
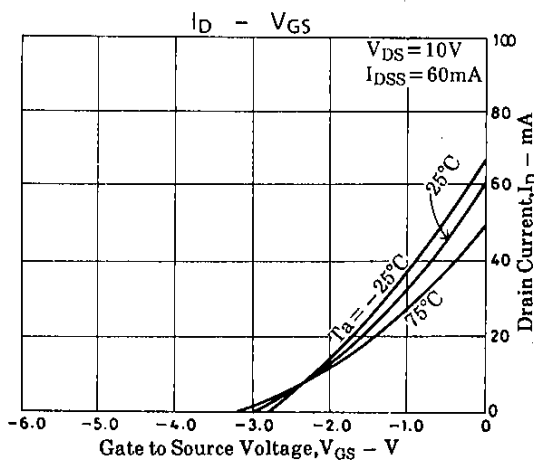
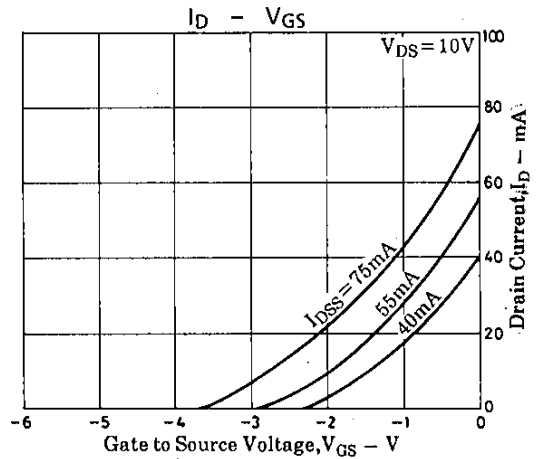
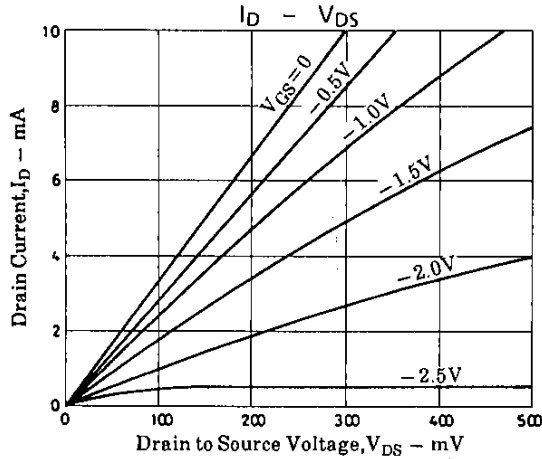
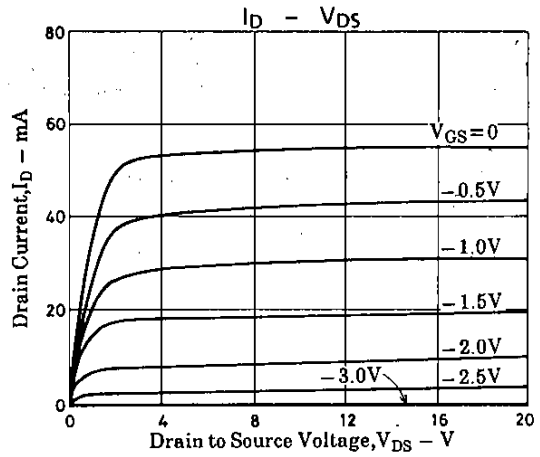
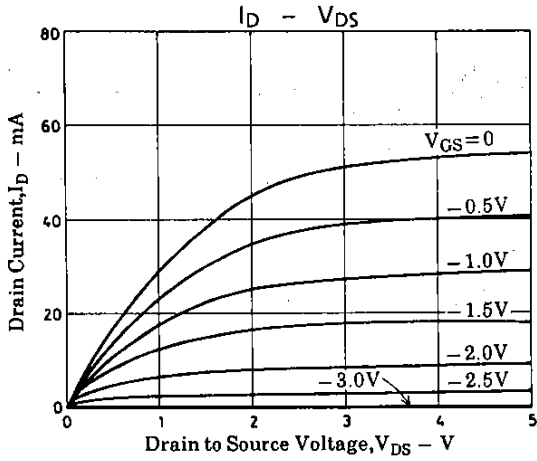
Marking : IJ  
 $I_{DSS}$  rank : 3,4,5

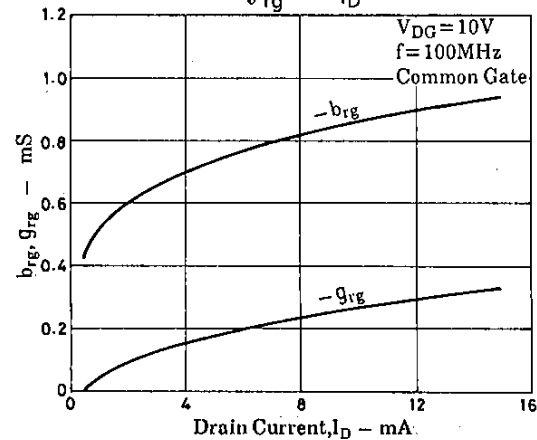
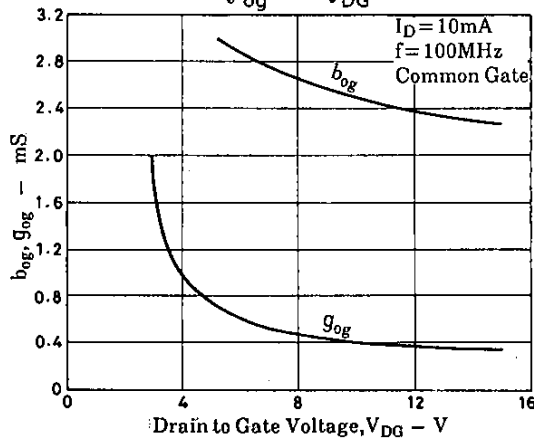
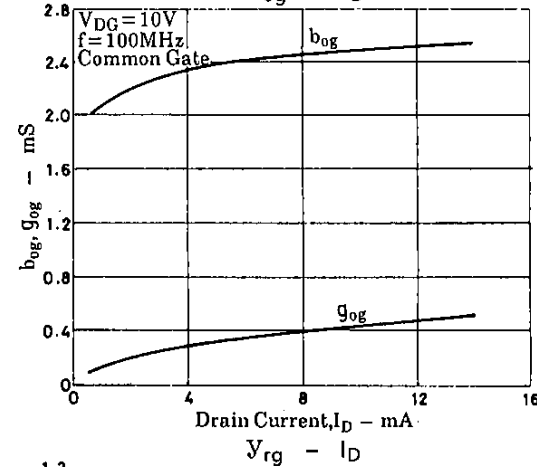
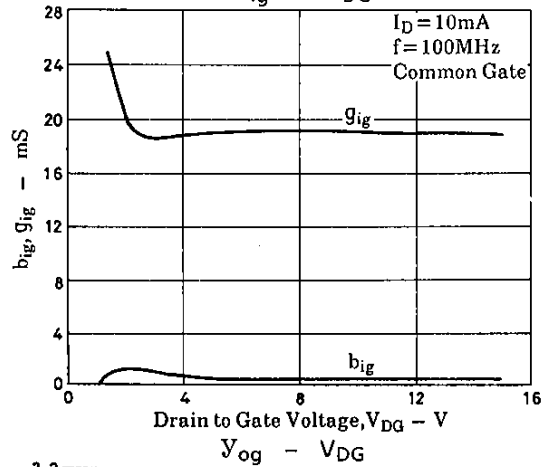
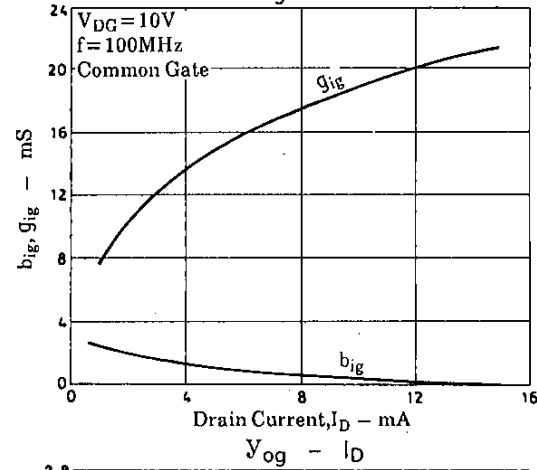
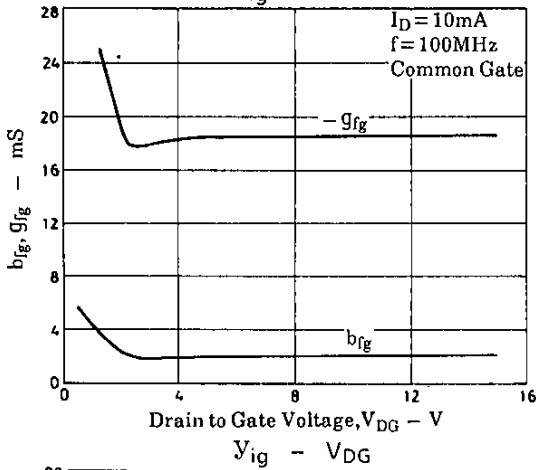
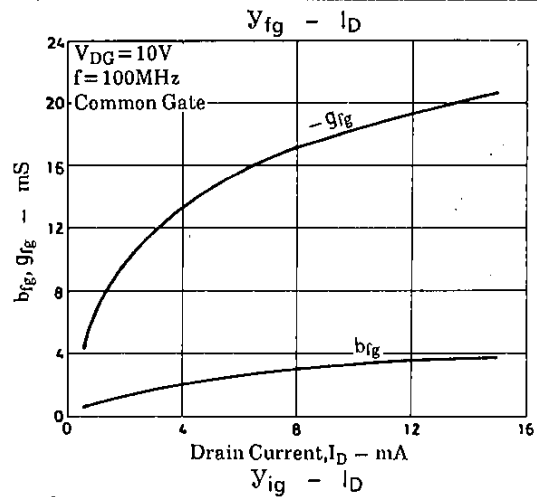
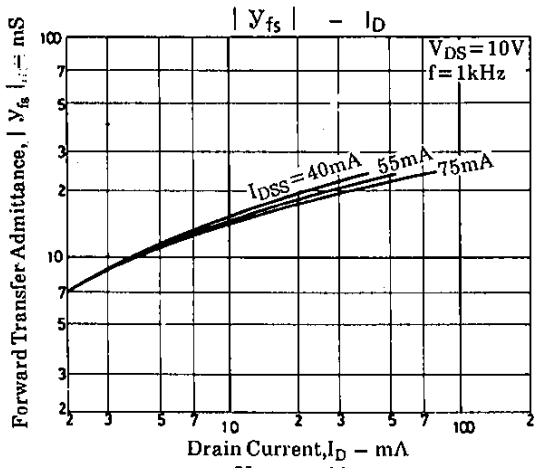
**Package Dimensions 2050**

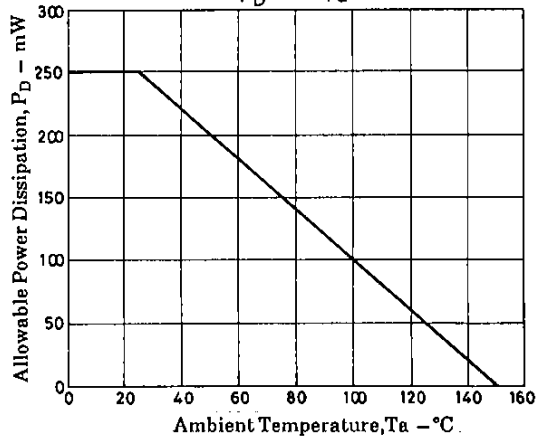
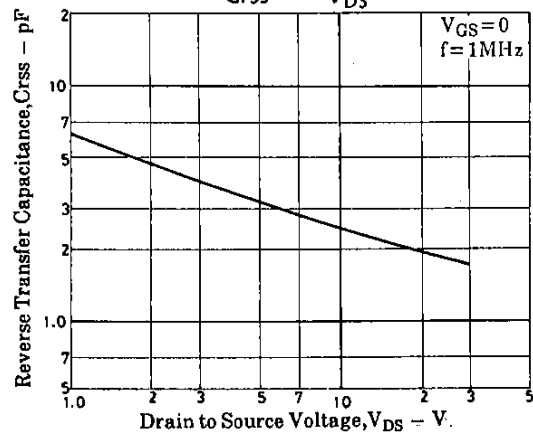
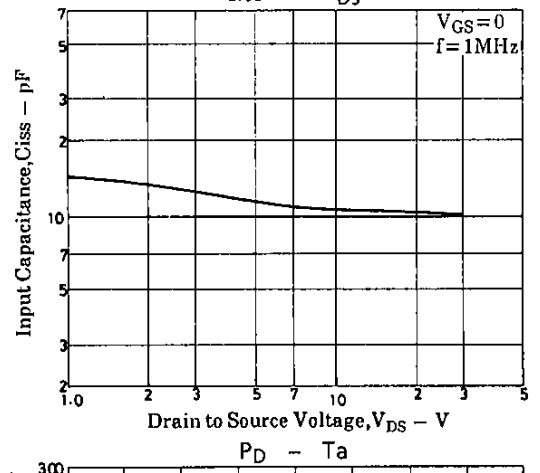
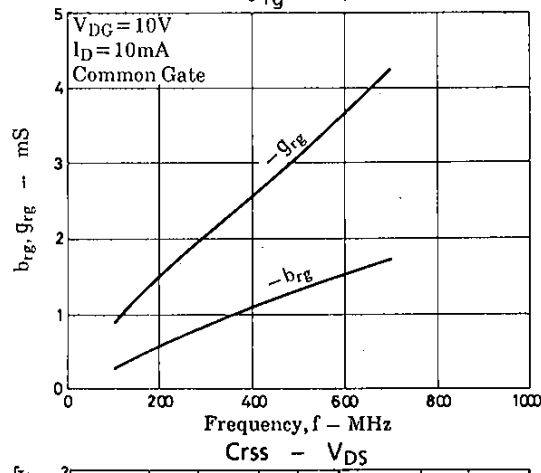
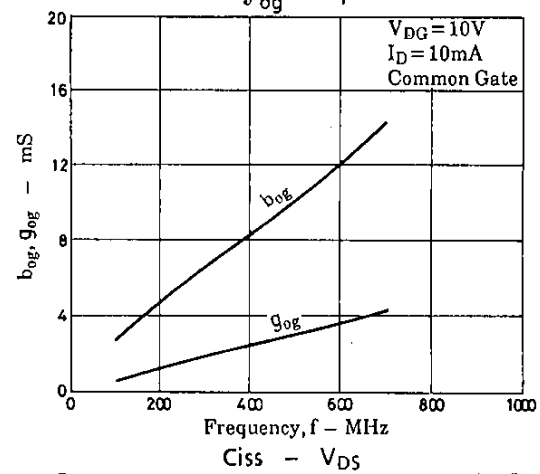
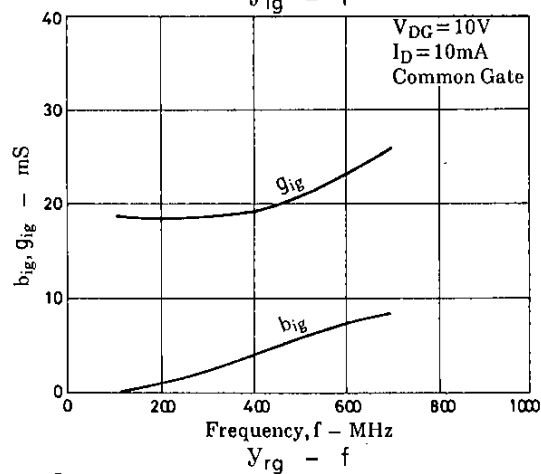
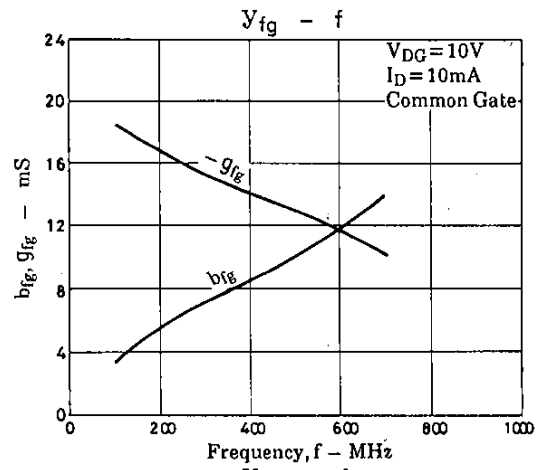
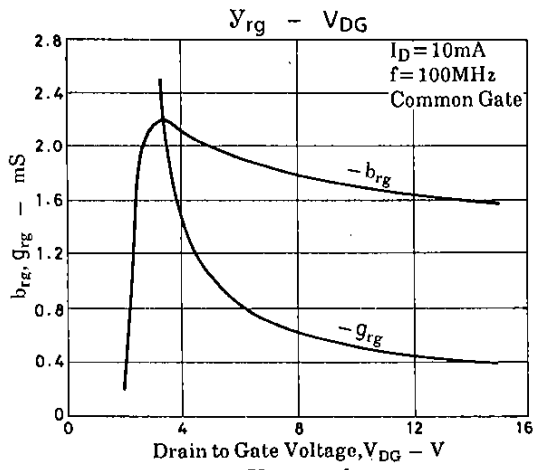
(unit : mm)



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